

Taiwan Semiconductor

200mW High Speed SMD Switching Diode

FEATURES

- Fast switching device (trr<4.0ns)
- Surface mount device type
- Moisture sensitivity level 1
- Matte Tin (Sn) lead finish
- Pb free version and RoHS compliant
- Packing code with suffix "G" means green compound (halogen-free)

MECHANICAL DATA

- Case: Flat lead SOD-323F small outline plastic package
- Terminal: Matte tin plated, lead free., solderable per MIL-STD-202, Method 208 guaranteed
- High temperature soldering guaranteed : 260°C/10s
- Polarity: Indicated by cathode band
- Weight: 4.85 ± 0.5 mg









|--|--|

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (T _A =25°C unless otherwise noted)				
PARAMETER	SYMBOL	VALUE	UNIT	
Power Dissipation	P _D	200	mW	
Non-Repetitive Peak Reverse Voltage	V _{RM}	100	V	
Repetitive Peak Reverse Voltage	V_{RRM}	75	V	
Reverse Voltage	V _R	100	V	
Non-Repetitive Peak Forward Current	I _{FRM}	300	mA	
Mean Forward Current	Io	150	mA	
Thermal Resistance (Junction to Ambient)	R _{eJA}	625	°C/W	
Junction and Storage Temperature Range	T_J,T_STG	-65 to + 150	°C	

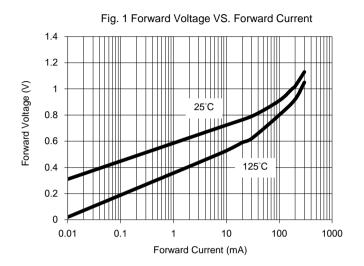
PARAMETER			SYMBOL	MIN	MAX	UNIT
Doverso Brookdows Volte		I _R =100μA		100	-	V
Reverse Breakdown Volta	age	I _R =5μA	$V_{(BR)}$	75	-	V
Forward Voltage						
	1N4448WS, 1N914BWS	$I_F=5.0mA$	V _F	0.62	0.72	V
	1N4148WS	$I_F=10.0mA$	V F	-	1.0	v
	1N4448WS, 1N914BWS	$I_F=100.0mA$		-	1.0	
Boyeroo Lookogo Curron	4	$V_R=20V$	1		25	nA
Reverse Leakage Curren	l	$V_R=75V$	I _R	-	5.0	μΑ
Junction Capacitance V _R =0, f=1.0MHz		CJ	-	4.0	pF	
Reverse Recovery Time	I _F =10mA, I _R =60mA, R	L=100Ω, I _{RR} =1mA	t _{rr}	-	4.0	ns

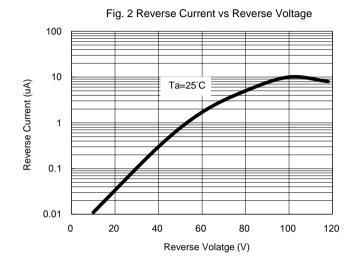
Version: I1603

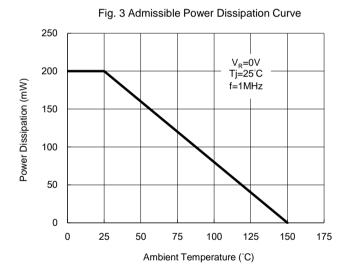


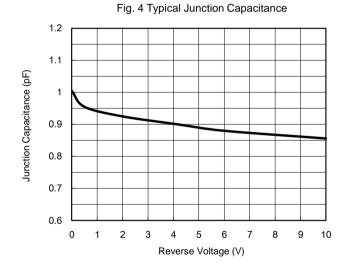
RATINGS AND CHARACTERISTICS CURVES

(T_A=25°C unless otherwise noted)









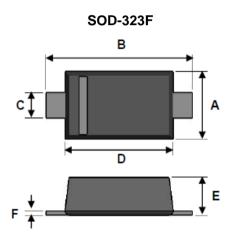


ORDERING INFORMATION				
PART NO.	PACKING CODE	PACKING CODE SUFFIX	PACKAGE	PACKING
1NxxxxWS (Note 1)	RR	G	SOD-323F	3K / 7" Reel

Note 1: "xxxx" is Device Code from "4148" to "914B".

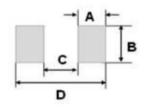
EXAMPLE				
PREFERRED P/N	PART NO.	PACKING CODE	PACKING CODE	DESCRIPTION
1N4148WS RRG	1N4148WS	RR	G	Green compound

DIMENSIONS



DIM.	Unit (mm)		Unit ((inch)
DIIVI.	Min	Max	Min	Max
Α	1.15	1.35	0.045	0.053
В	2.30	2.80	0.091	0.110
С	0.25	0.40	0.010	0.016
D	1.60	1.80	0.063	0.071
Е	0.80	1.10	0.031	0.043
F	0.05	0.25	0.002	0.010

SUGGESTED PAD LAYOUT



DIM.	Unit (mm)	Unit (inch)
Dilvi.	Тур.	Тур.
Α	0.630	0.025
В	0.830	0.033
С	1.600	0.063
D	2.860	0.113

Note: 1. The suggested land pattern dimensions have been provided for reference only, as actual pad layouts may vary depending on application.

MARKING

Part No.	Marking
1N4148WS	S1
1N4448WS	S2
1N914BWS	S3

Version: I1603



Taiwan Semiconductor

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.

Version: I1603